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Initial studies of irradiated Ga doped LGADs

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LGADs have been produced by CNM where Ga replaced B as a dopant in the multiplication layer in order to increase radiation hardness of LGADs. Although the devices exhibited early breakdown before irradiations they were fully functional after neutron irradiation. TCT and charge collection measurements with 90Sr were performed on devices irradiated up to the equivalent fluences of 6e15 cm-2. Initial studies indicate that Ga doped devices can be more radiation hard that the B doped ones.

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